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The crystal defect region 11 is irradiated by the electron beams radiated from above after removing the resist layer 84 as shown in Fig. 8. The radiation of the beams is carried out at 1 mega electro-volts in energy strength in this embodiment.

IN THE CLAIMS

Please amend claim 9 to read as follows:

- Sub F' E3
9. (Twice Amended) A semiconductor device comprising:
- a substrate having a region irradiated with radiating rays,
 - crystal defects within the region irradiated, and
 - a metal wiring layer located over the substrate, the metal wiring layer being made of a light metal, the metal wiring layer having an opening above the region irradiated, so that radiating rays passing to the region irradiated through the opening generate the crystal defects only under the opening.